



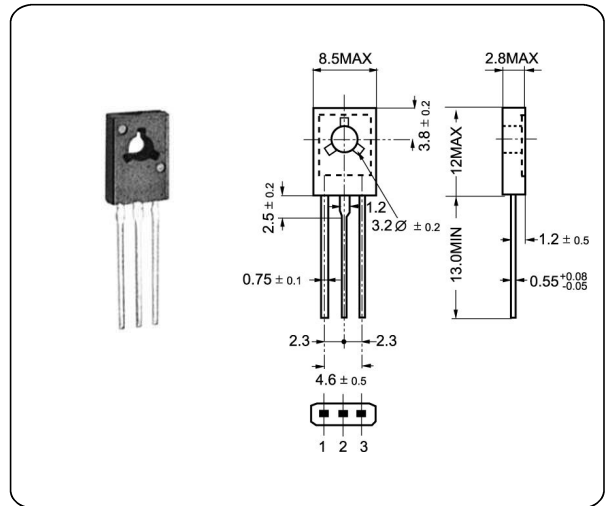
## Thyristors logic level

## C106M

### GENERAL DESCRIPTION

Passivated, sensitive gate thyristor in a plastic envelope, intended for use in general purpose switching and phase control applications. This device is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits

Parameter	Symbol	Max	Unit
Repetitive peak off-state voltages	$V_{DRM}$ $V_{RRM}$	400	V
Average on-state current	$I_{T(AV)}$	2.5	A
RMS on-state current	$I_{T(RMS)}$	4.0	A
Non-repetitive peak on-state current	$I_{TSM}$	38	A
Max. Operating Junction Temperature	$T_j$	110	°C
Storage Temperature	$T_{stg}$	-45~150	°C



Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	$V_{DRM}$ $V_{RRM}$		400			V
Average on-state current	$I_{T(AV)}$	half sine wave; $T_{mb} < 103\text{ °C}$		2.5		A
RMS on-state current	$I_{T(RMS)}$	all conduction angles		4.0		A
On-state voltage	$V_T$	$I_T = 5.0\text{ A}$		1.23	1.8	V
Holding current	$I_H$	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$		0.1	6.0	mA
Latching current	$I_L$	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$		0.17	10	mA
Gate trigger current	$I_{GT}$	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$		15	200	uA
Gate trigger voltage	$V_{GT}$	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$		0.4	1.5	V